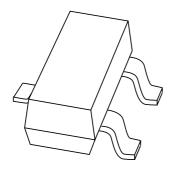
## DISCRETE SEMICONDUCTORS

# DATA SHEET



# PMBD7100 High-speed double diode

Product data sheet 2003 Nov 07



## **High-speed double diode**

### **PMBD7100**

#### **FEATURES**

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 100 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 450 mA.

#### **APPLICATIONS**

• High-speed switching in thick and thin-film circuits.

#### **DESCRIPTION**

The PMBD7100 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the small SOT23 SMD plastic package.

#### **MARKING**

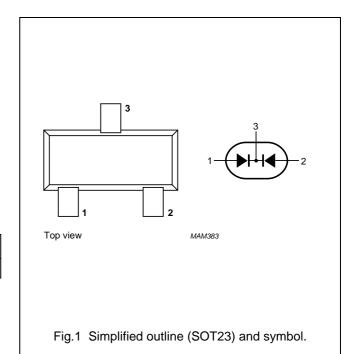
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMBD7100	*3A

#### Note

- 1. \* = p: made in Hong Kong.
  - \* = t: made in Malaysia.
  - \* = W: made in China.

#### **PINNING**

PIN	DESCRIPTION			
1	anode (a1)			
2	anode (a2)			
3	common connection			



#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE			
TIPE NUMBER	NAME DESCRIPTION				
PMBD7100	-	plastic surface mounted package; 3 leads	SOT23		

# High-speed double diode

PMBD7100

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT				
Per diode									
$V_{RRM}$	repetitive peak reverse voltage		_	100	V				
$V_R$	continuous reverse voltage		_	100	V				
I <sub>F</sub>	continuous forward current	single diode loaded; see Fig.2; note 1	_	215	mA				
		double diode loaded; see Fig.2; note 1	_	125	mA				
I <sub>FRM</sub>	repetitive peak forward current		_	450	mA				
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4							
		$t_p = 1 \mu s$	_	4	Α				
		$t_p = 1 \text{ ms}$	_	1	Α				
		t <sub>p</sub> = 1 s	_	0.5	Α				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	250	mW				
T <sub>stg</sub>	storage temperature		-65	+150	°C				
Tj	junction temperature		_	150	°C				

#### Note

<sup>1.</sup> Device mounted on an FR4 printed-circuit board.

# High-speed double diode

PMBD7100

#### **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT					
Per diode									
V <sub>F</sub>	forward voltage	see Fig.3							
		I <sub>F</sub> = 1 mA	715	mV					
		I <sub>F</sub> = 10 mA	855	mV					
		I <sub>F</sub> = 50 mA	1	V					
		I <sub>F</sub> = 150 mA	1.25	V					
$I_R$	reverse current	see Fig.5							
		V <sub>R</sub> = 25 V	30	nA					
		V <sub>R</sub> = 100 V	2.5	μΑ					
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	60	μΑ					
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 150 °C	100	μΑ					
$C_{d}$	diode capacitance	$V_R = 0 V$ ; $f = 1 MHz$ ; see Fig.6	1.5	pF					
t <sub>rr</sub>	reverse recovery time	when switched from $I_F$ = 10 mA to $I_R$ = 10 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.7	4	ns					
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 10$ mA to $t_r = 20$ nA; see Fig.8	1.75	V					

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point		360	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

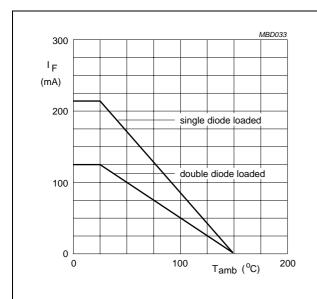
1. Device mounted on an FR4 printed-circuit board.

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## High-speed double diode

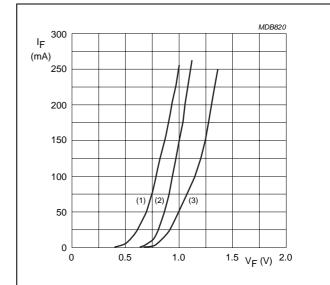
PMBD7100

#### **GRAPHICAL DATA**



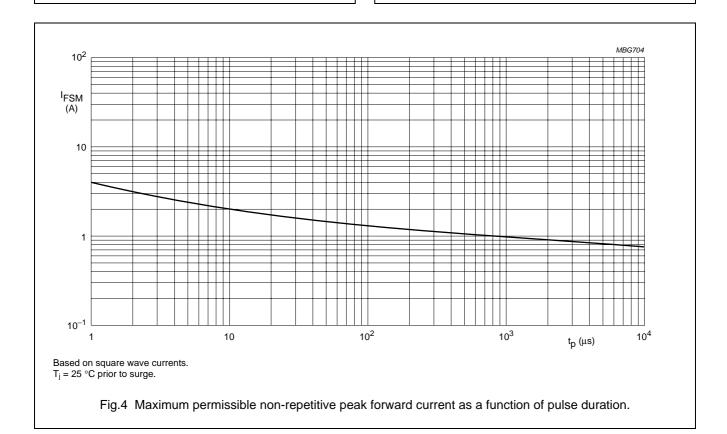
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



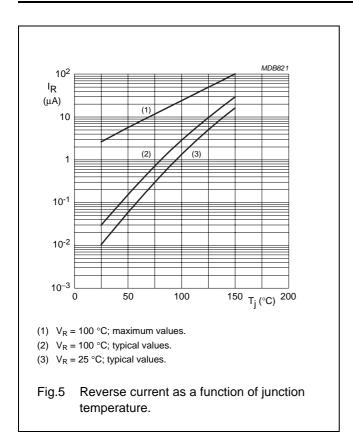
- (1)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25 \,^{\circ}\text{C}$ ; maximum values.

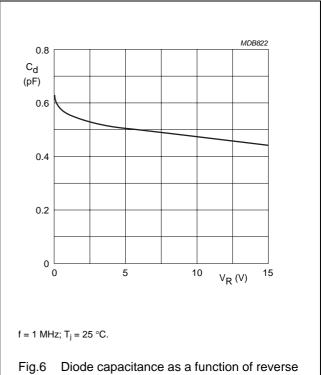
Fig.3 Forward current as a function of forward voltage.



# High-speed double diode

### PMBD7100



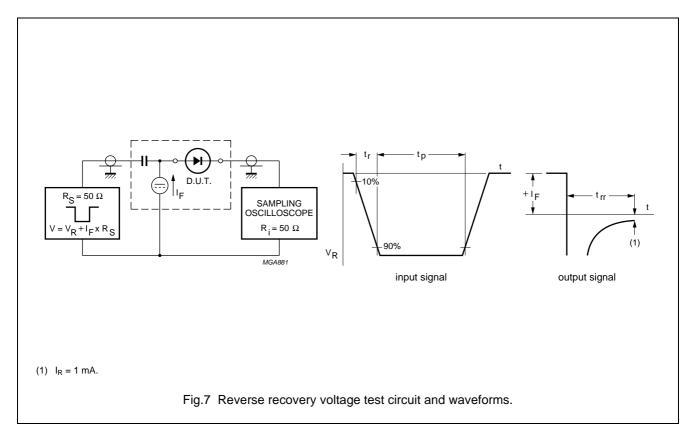


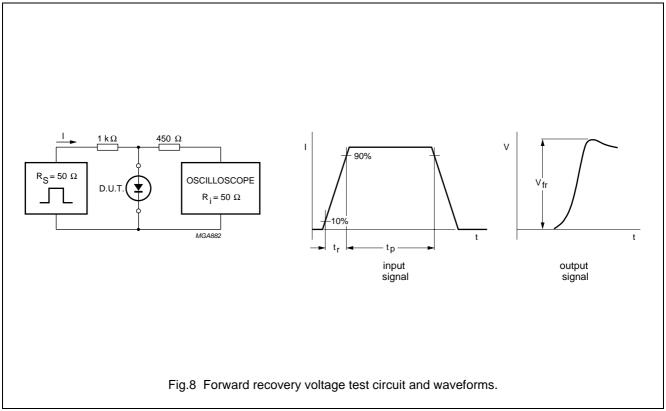
voltage; typical values.

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# High-speed double diode

### PMBD7100





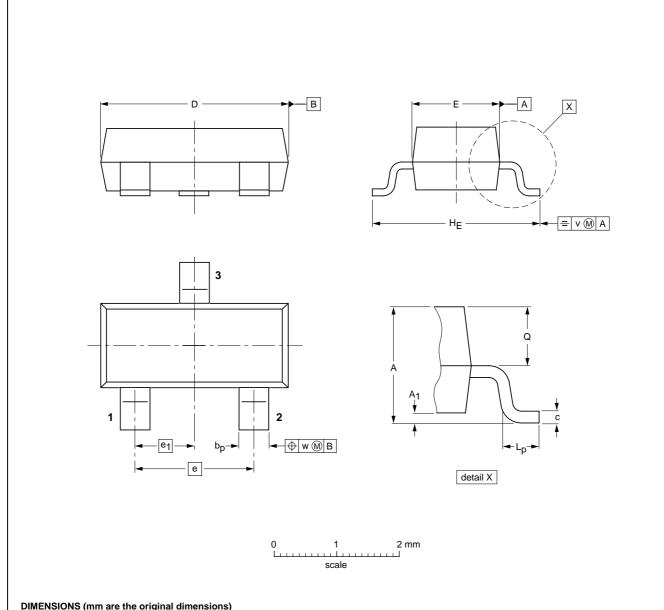
# High-speed double diode

PMBD7100

#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm	are the	original	dimensions)
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UN	IT	A	A <sub>1</sub> max.	bp	C	D	E	е	e <sub>1</sub>	HE	L <sub>p</sub>	Q	٧	w
mı	n	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				<del>-97-02-28</del> 99-09-13	

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### High-speed double diode

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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